METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE WITH A STRAINED CHANNEL

ABSTRACT

A method of manufacturing a semiconductor device provides a semiconductor substrate with a gate and a number of source/drain regions on the semiconductor substrate. A layer containing a strain-inducing element is provided over the number of source/drain regions. The strain-inducing element is driven from the layer containing a strain-inducing element into the number of source/drain regions. A number of source/drains is formed in the number of source/drain regions.

FIG 5.